

EXHIBIT 14

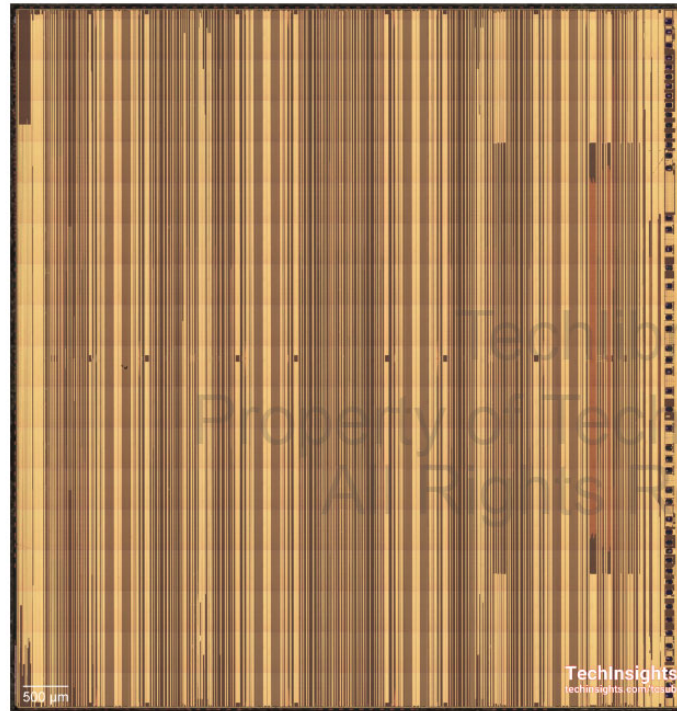
U.S. Patent No. 6,781,858

Claim 21	Identification: Lenovo Moto G Power mobile phone ¹									
21. A cubic memory array, comprising:	<div><div></div><div><div><div>moto g POWER</div><div>Go up to three days[†] on a single charge thanks to a 5000 mAh battery.</div><div>16MP triple camera system. Capture ultra-wide angle panoramas, sharper portraits, and super detailed close-up shots.</div><div>Dual Stereo Speakers tuned by Dolby[®].</div></div><div><table><tr><td>Operating system Android™ 10</td><td>Internal storage 64GB built-in^{††}</td><td>Sensors Accelerometer, Gyroscope, Proximity, Ambient Light, Sensor Hub, Fingerprint reader, magnetometer (e-compass)</td></tr><tr><td>Processor Qualcomm® Snapdragon™ 665 Mobile Processor</td><td>Expandable Storage up to 512GB microSD card expandable^{†††}</td><td>Memory (RAM) 4GB</td></tr><tr><td colspan="3">Security Rear fingerprint reader</td></tr></table></div></div></div>	Operating system Android™ 10	Internal storage 64GB built-in ^{††}	Sensors Accelerometer, Gyroscope, Proximity, Ambient Light, Sensor Hub, Fingerprint reader, magnetometer (e-compass)	Processor Qualcomm® Snapdragon™ 665 Mobile Processor	Expandable Storage up to 512GB microSD card expandable ^{†††}	Memory (RAM) 4GB	Security Rear fingerprint reader		
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Processor Qualcomm® Snapdragon™ 665 Mobile Processor	Expandable Storage up to 512GB microSD card expandable ^{†††}	Memory (RAM) 4GB								
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	<div><div><div>https://www.motorola.ca/smartphones-moto-g-power/p?skuId=13 https://www.gsmarena.com/motorola_moto_g_power-10076.php</div></div></div>									

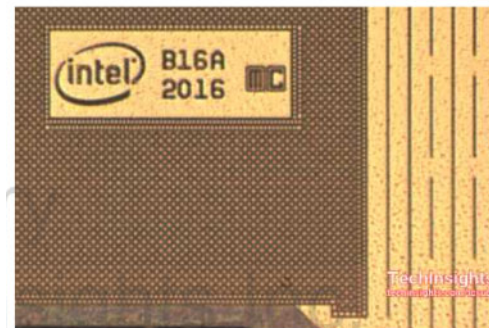
¹ Additional infringing Lenovo devices sold or offered for sale by Verizon, including at least Motorola G Pure, Moto G Play, Moto G7 Play, Moto G Fast devices.

On information and belief, Lenovo Moto G Power mobile phones contain a Micron MT29VZZZAD8QKSL-046 multi-chip module with LPDDR4 SDRAM (Z11N die), 3D NAND Flash (B16A die), and eMMC controller (PS8226 die).

A 3D NAND flash array is a cubic memory array.

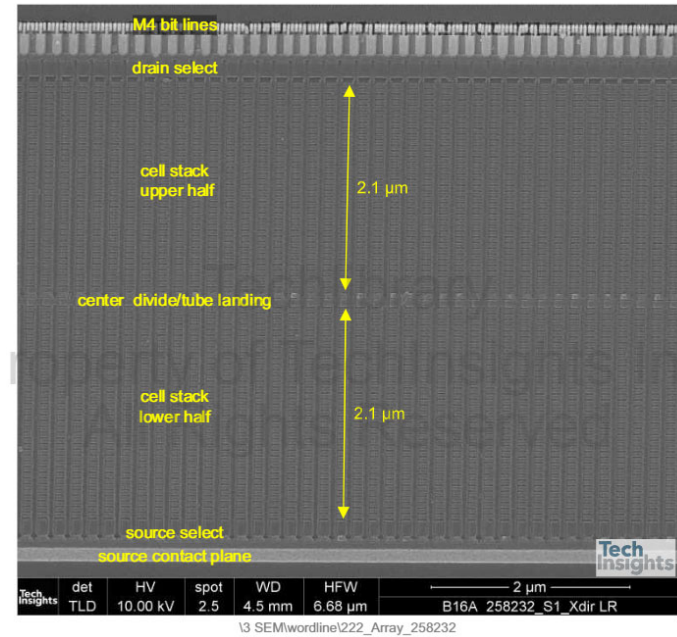
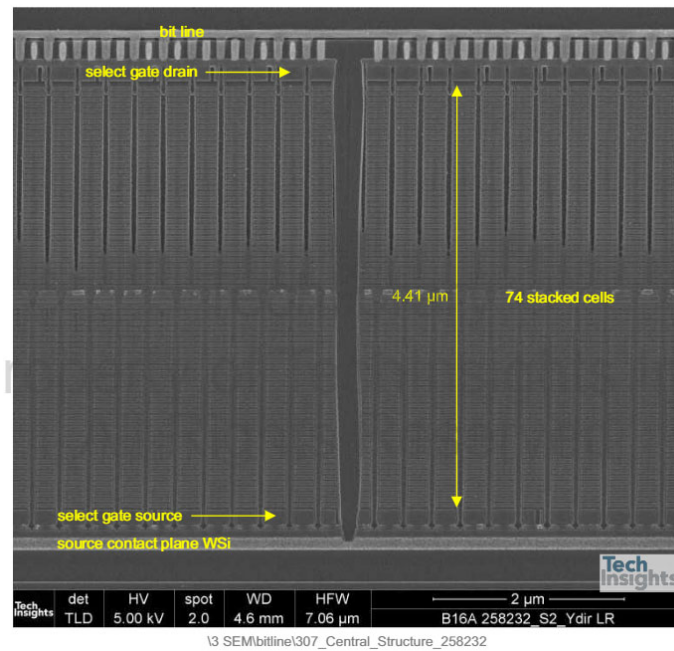


\\2 Package_and_Die_Photos\X-rays_and_Optical\29F01T2ANCH2_B16A_256107_Oriented



\\2 Package_and_Die_Photos\X-rays_and_Optical\29F01T2ANCH2_B16A_256107_DieMrk-50XRotated

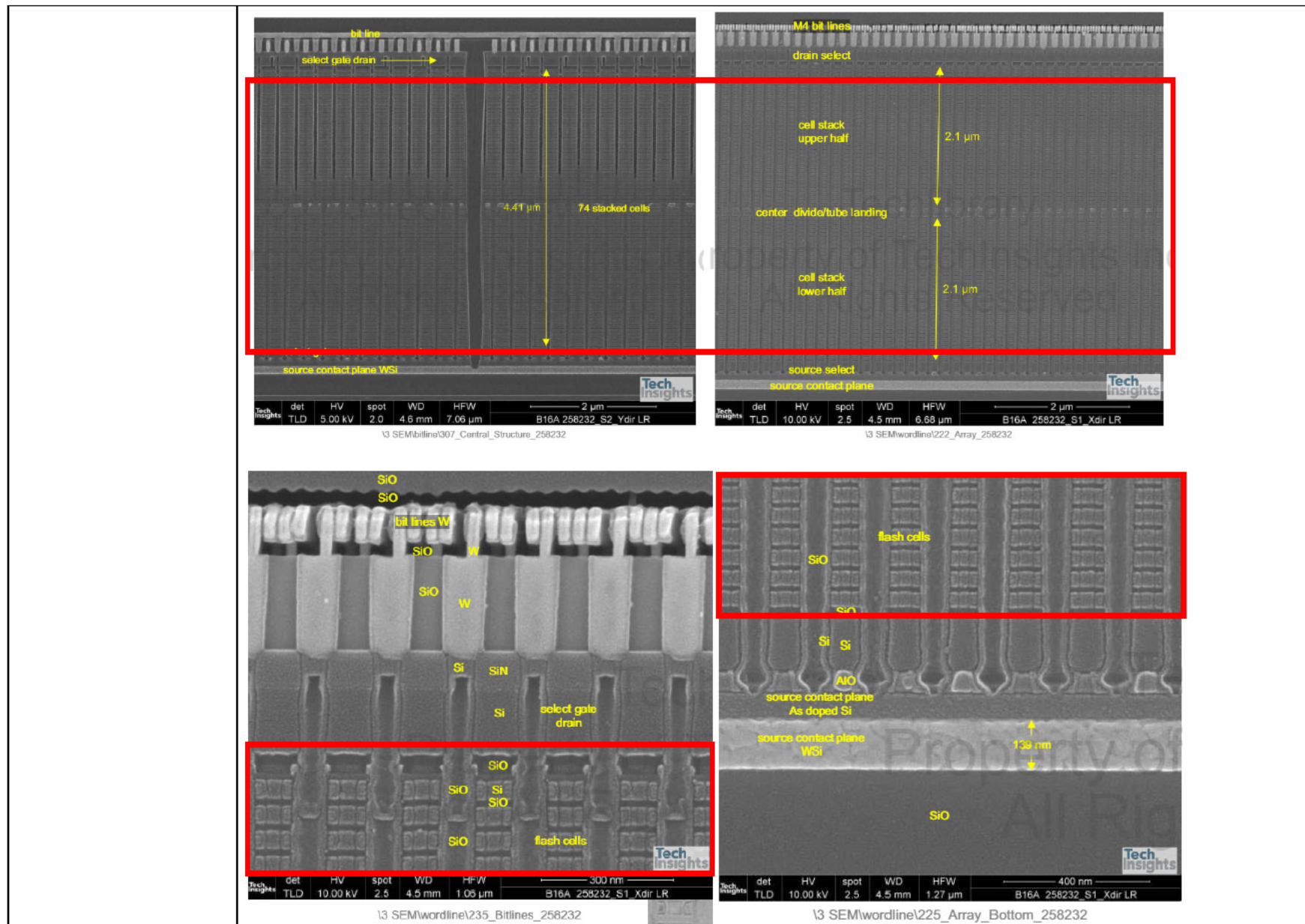
Techinsights, “Intel 29F01T2ANCH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018

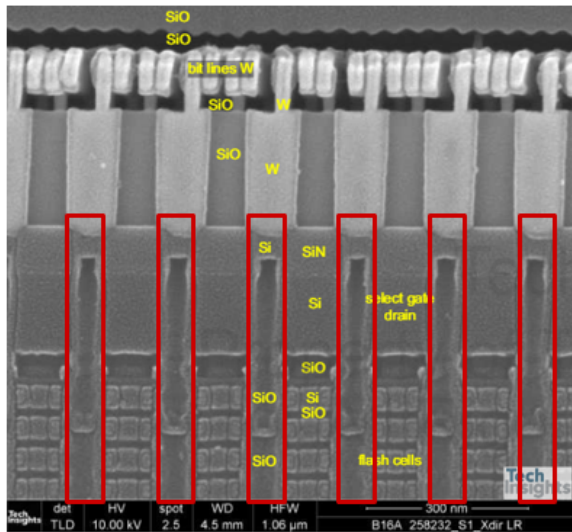
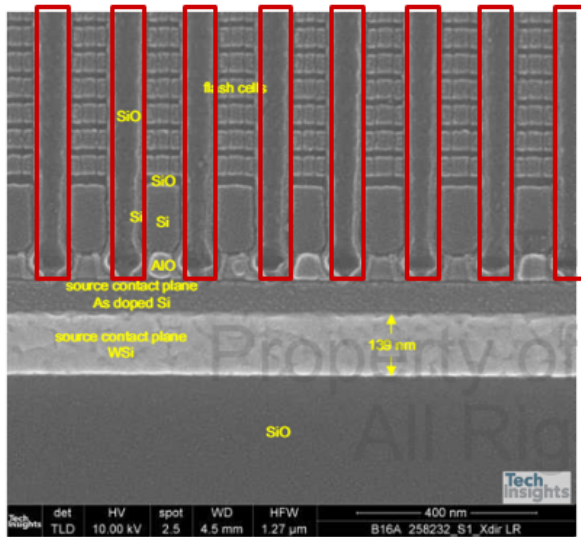


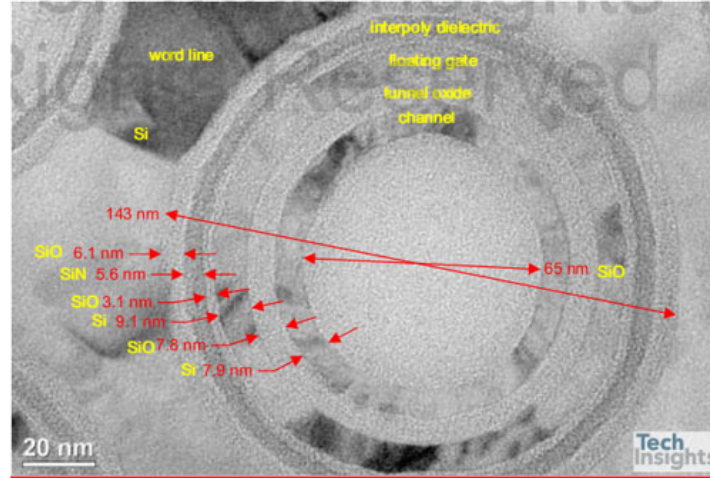
Techinsights, "Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash", report AME-1707-801.pdf, March 2018

a plurality of horizontal select lines;

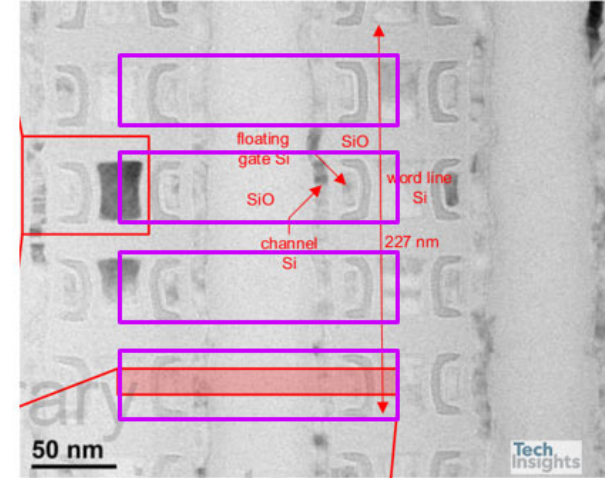
The 3D NAND Flash array has a plurality of wordlines, which are horizontal select lines.



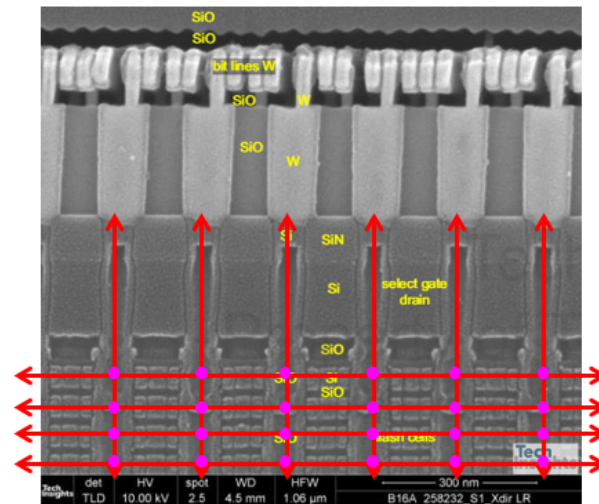
	<p>Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018</p>
<p>a plurality of vertical select lines;</p>	<p>The 3D NAND Flash array has a plurality of vertical select lines.</p> <div style="display: flex; justify-content: space-around;">   </div> <p>Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018</p>
<p>a plurality of memory cells, each memory cell adjacent to a horizontal select line and adjacent to a vertical select line; and</p>	<p>The 3D NAND Flash array has a plurality of floating gate memory cells, each memory cell adjacent to a horizontal select line and adjacent to a vertical select line.</p>



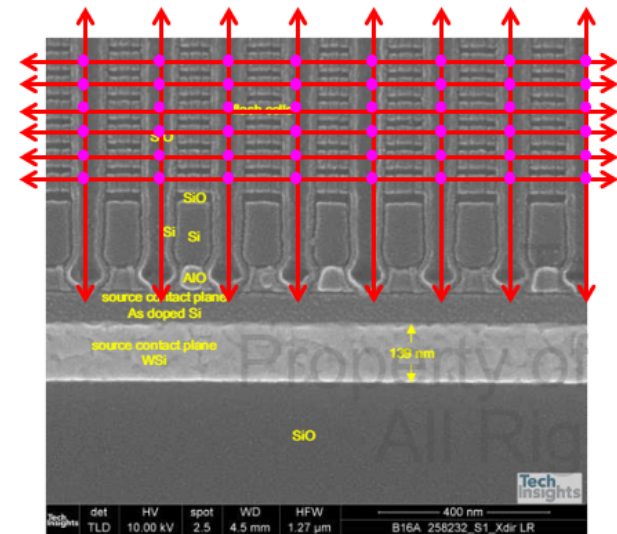
I4 TEM/bevel/cells near middle 130k_257788



I4 TEM/wordline/cells e 64k 2_257787

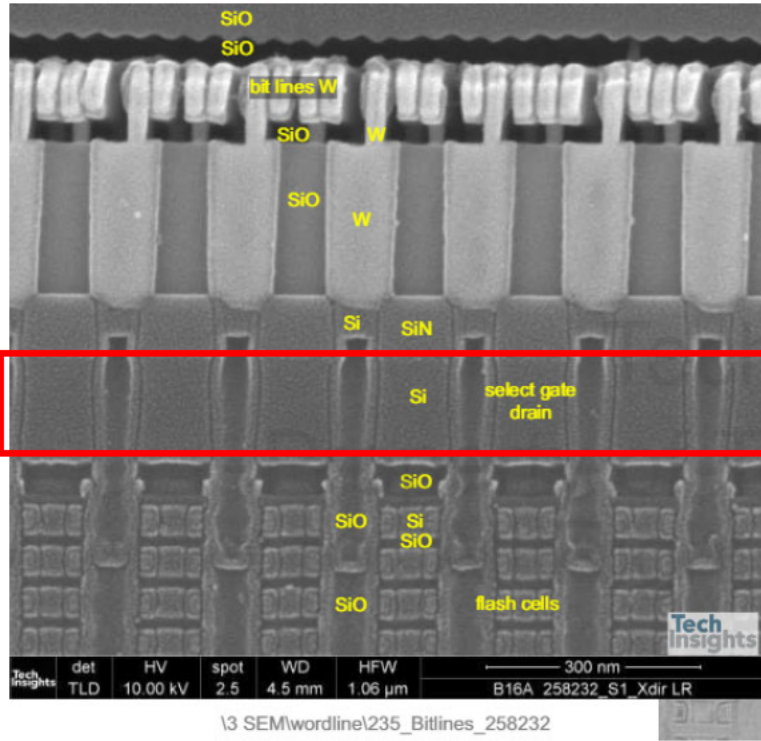


I3 SEM/wordline/235_Balllines_258232

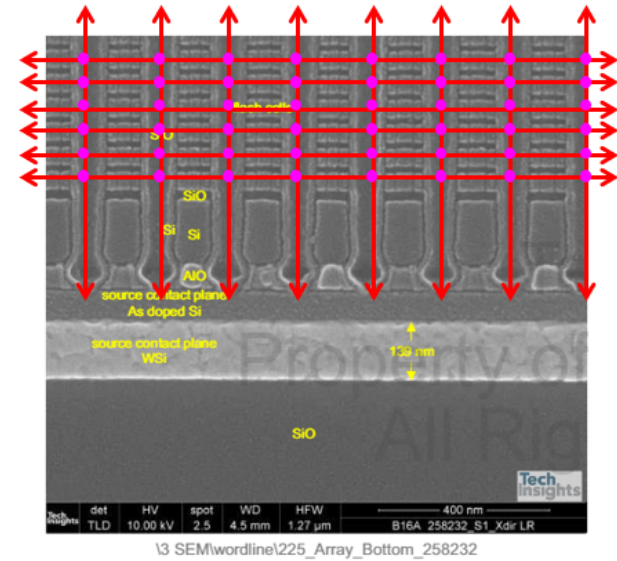
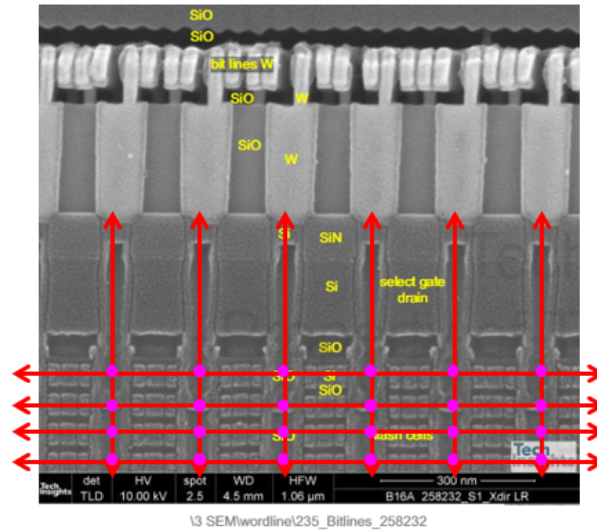


I3 SEM/wordline/225_Array_Bottom_258232

Techinsights, "Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash", report AME-1707-801.pdf, March 2018

<p>at least one switching element disposed on top of at least one of the plurality of vertical select lines;</p>	<p>The 3D NAND Flash array has at least one switching element (select gate drain) disposed on top of at least one of the plurality of vertical select lines.</p>  <p>Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018</p>
<p>wherein the plurality of memory cells are arranged to form planes of horizontal select lines and planes of vertical</p>	<p>The 3D NAND Flash array has the plurality of memory cells arranged to form planes of horizontal select lines and planes of vertical select lines orthogonal to each other.</p>

select lines
orthogonal to each
other.



Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018